

1200V 32mohm Silicon Carbide Power MOSFET

AK1CK2M032WAMH

Features:

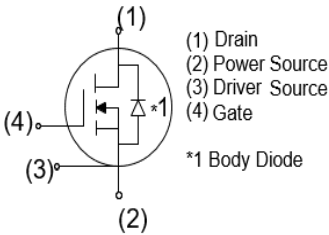
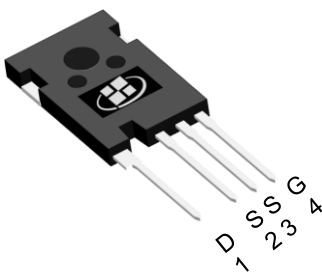
- Low on-resistance
- Fast switching speed with low capacitances
- Fast intrinsic diode with low reverse recovery (Q_{rr})
- Halogen-free, RoHS compliant

Applications:

- Motor drives
- Switched mode power supplies

Key Performance Parameters:

Parameter	Value	Unit
V_{DS}	1200	V
$R_{DS(on),\text{ TYP}} @V_{GS} = 18\text{ V}$	27	m Ω
I_D	80	A
P_D	348	W



Ordering Information:

Ordering Code	Package Type	Marking Code	Form	Packing
AK1CK2M032WAMH	TO-247-4L	1CK2M032WAMH	Tube	See the detail package information

Maximum Ratings (T_A = 25°C unless otherwise noted)

Symbol	Parameter	Value	Units
V _{DS}	Drain-Source Voltage	1200	V
I _D	Drain Current - Continuous (T _C = 25°C) ^(Note 1)	80	A
	Drain Current - Continuous (T _C = 100°C) ^(Note 1)	56.5	A
I _{DM}	Drain Current - Pulsed ^(Note 2)	120	A
V _{GS}	Gate - Source Voltage (dynamic)	-10/+22	V
V _{GS}	Gate - Source Voltage (static)	-6/+18	V
P _D	Power Dissipation (T _C = 25°C)	348	W
T _J , T _{STG}	Operating and Storage Temperature Range	-55 to +175	°C

Thermal Characteristics

Symbol	Parameter	Value	Units
R _{θJC}	Thermal Resistance, Junction - to - Case, Steady - State	0.43	°C/W
R _{θJA}	Thermal Resistance, Junction - to - Ambient, Steady - State	40	°C/W

- Notes:
- 1. The max drain current limited by maximum junction temperature
 - 2. Repetitive Rating: Pulse width limited by maximum junction temperature

Electrical Characteristics (T _J = 25°C unless otherwise noted)						
Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Static Characteristics						
V _{(BR)DSS}	Drain - Source Breakdown Voltage	V _{GS} = 0 V, I _D = 100 μA	1200			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 1200 V, V _{GS} = 0 V		5	50	μA
I _{GSS}	Gate Leakage Current	V _{GS} = + 22 V, V _{DS} = 0 V			100	nA
		V _{GS} = - 10 V, V _{DS} = 0 V			-100	nA
V _{GS(th)}	Gate Threshold voltage	V _{DS} = V _{GS} , I _D = 11.5 mA	2.2	3.2	4.2	V
		V _{DS} = V _{GS} , I _D = 11.5 mA, T _J = 175 °C		2.3		V
R _{DS(ON)}	Drain-Source on-state resistance	V _{GS} = 18 V, I _D = 40 A		27	38	mΩ
		V _{GS} = 18 V, I _D = 40 A, T _J = 175 °C		45		mΩ
g _{FS}	Forward Transconductance	V _{DS} = 20 V, I _D = 40 A		20		S
		V _{DS} = 20 V, I _D = 40 A, T _J = 175 °C		21		S
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} = 800 V, V _{GS} = 0 V, F = 100 kHz, V _{AC} = 25 mV		3550		pF
C _{OSS}	Output Capacitance			130		pF
C _{rss}	Reverse Transfer Capacitance			10		pF
E _{OSS}	C _{OSS} Stored Energy			55		μJ
R _g	Gate Resistance	F = 1 MHz, V _{AC} = 25 mV		1.2		Ω
Q _{gs}	Gate-Source Charge	V _{DS} = 800 V , I _D = 35 A, V _{GS} = -5/+18 V		45		nC
Q _{gd}	Gate-Drain Charge			62		nC
Q _g	Total Gate Charge			176		nC

Switching Characteristics						
Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
t _{d(on)}	Turn On Delay Time	V _{DD} = 800 V , I _D = 40 A, V _{GS} = -4/+18 V, R _{G,EXT} = 10 Ω L = 100 μH Diode: Body Diode at V _{GS} = -4V		17		ns
t _r	Rise Time			37		ns
t _{d(off)}	Turn Off Delay Time			56		ns
t _f	Fall Time			20		ns
E _{on}	Turn On Energy			850		μJ
E _{off}	Turn Off Energy			370		μJ
t _{d(on)}	Turn On Delay Time	V _{DD} = 800 V , I _D = 40 A, V _{GS} = -4/+18 V, R _{G,EXT} = 10 Ω L = 100 μH Diode: Body Diode at V _{GS} = -4V T _j = 175 °C		11		ns
t _r	Rise Time			36		ns
t _{d(off)}	Turn Off Delay Time			75		ns
t _f	Fall Time			23		ns
E _{on}	Turn On Energy			1720		μJ
E _{off}	Turn Off Energy			480		μJ
Drain-Source Diode Characteristics (T _j = 25 °C unless otherwise noted)						
I _S	Maximum Continuous Drain-Source Diode Forward Current				80	A
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current				120	A
V _{SD}	Diode Forward Voltage	V _{GS} = -4 V , I _{SD} = 20 A		5		V
		V _{GS} = -4 V , I _{SD} = 20 A, T _j = 175 °C		4.3		V
I _{rrm}	Peak Reverse Recovery Current	V _{GS} = -4 V , I _{SD} = 40 A, V _R = 800 V, di/dt = 2660 A/μs		27		A
t _{rr}	Reverse Recovery Time			18		ns
Q _{rr}	Reverse Recovery Charge			293		nC

Electrical Characteristics Diagrams

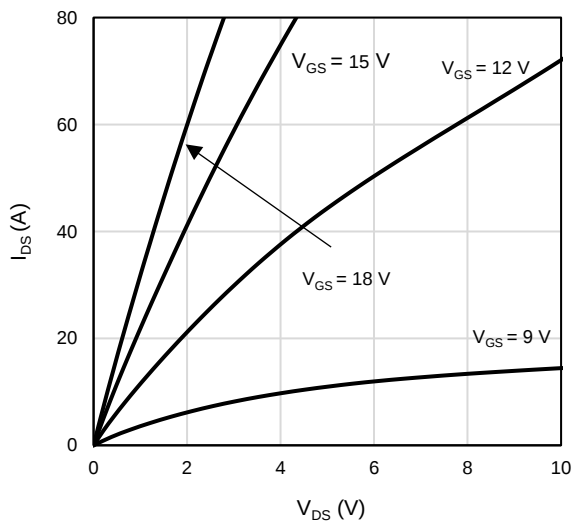
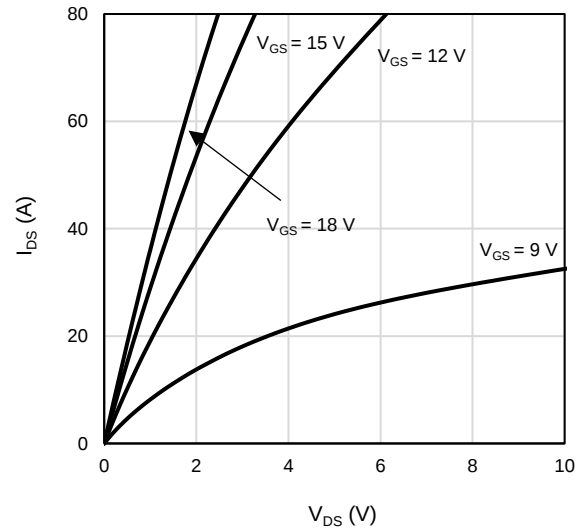
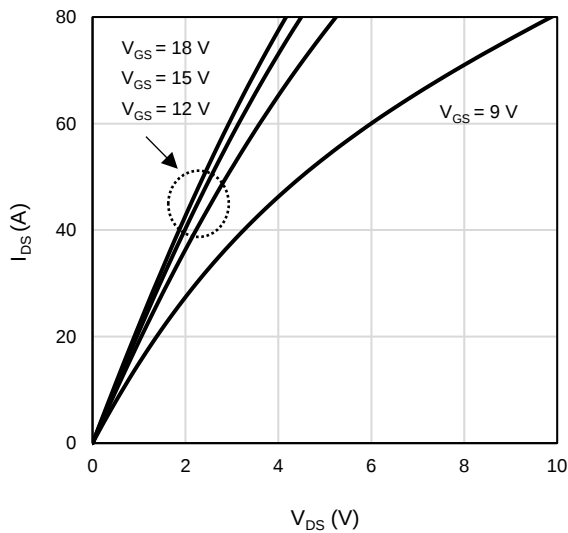
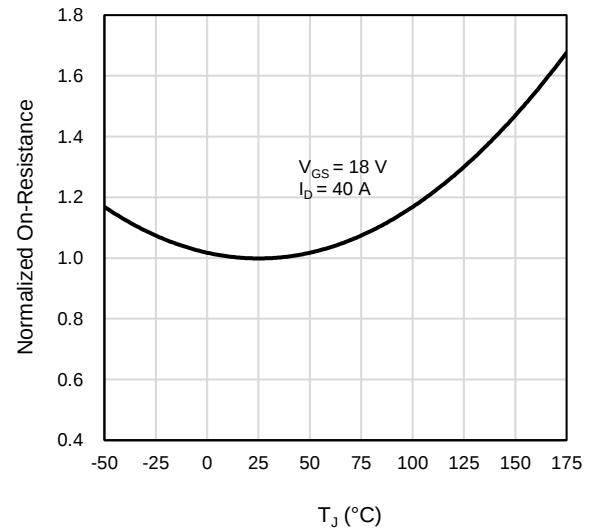
Figure 1: Output Characteristics $T_J = -40^{\circ}\text{C}$ Figure 2: Output Characteristics $T_J = 25^{\circ}\text{C}$ Figure 3: Output Characteristics $T_J = 175^{\circ}\text{C}$ 

Figure 4: Normalized On-Resistance vs. Temperature

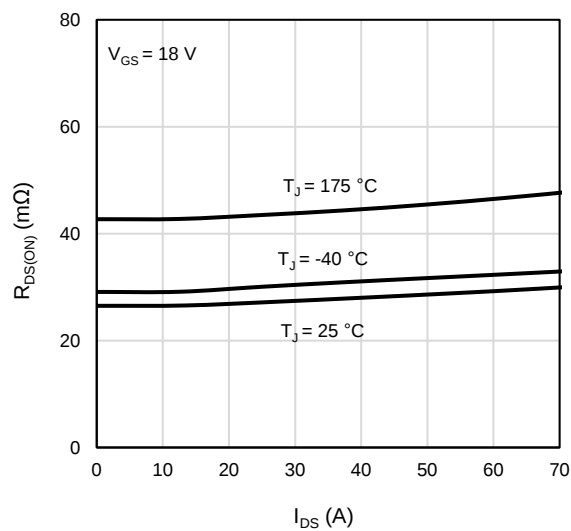


Figure 5: On-Resistance vs. Drain Current For Various Temperatures

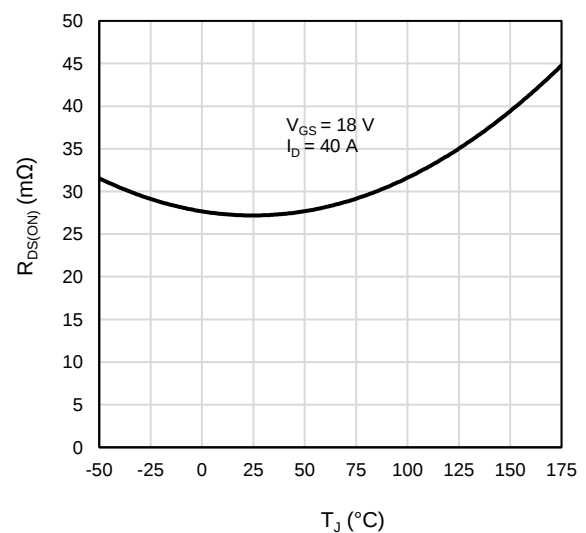


Figure 6: On-Resistance vs. Temperature

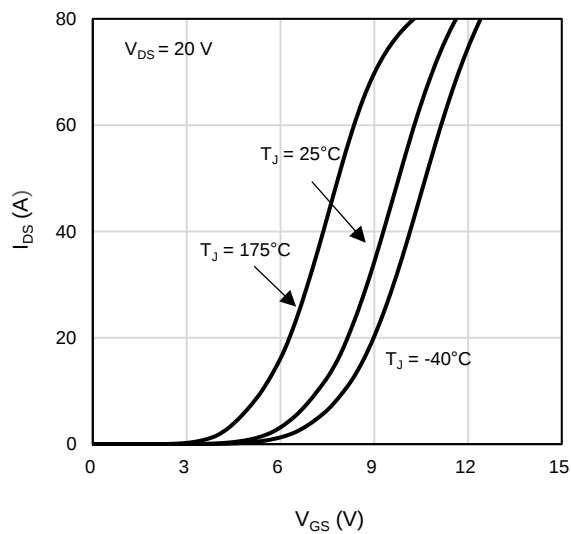


Figure 7: Transfer Characteristics For Various Junction Temperature

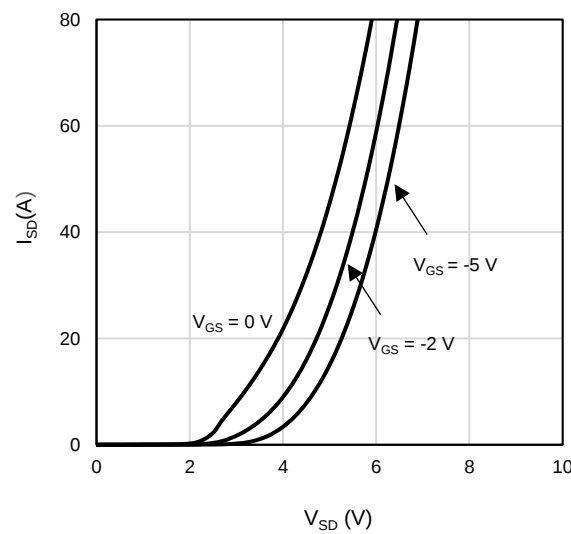


Figure 8: Body Diode Characteristics at -40°C

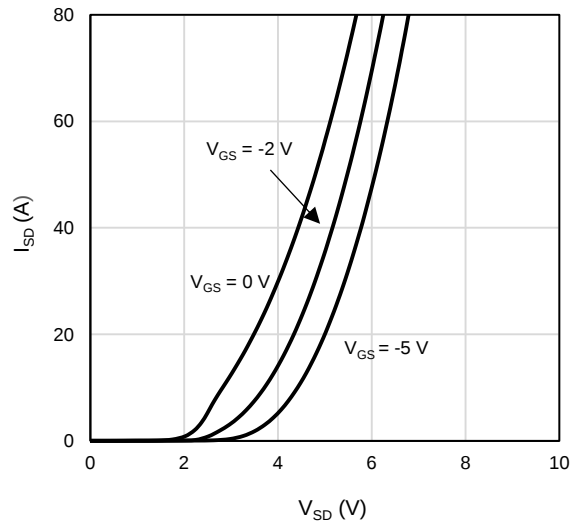


Figure 9: Body Diode Characteristics at 25°C

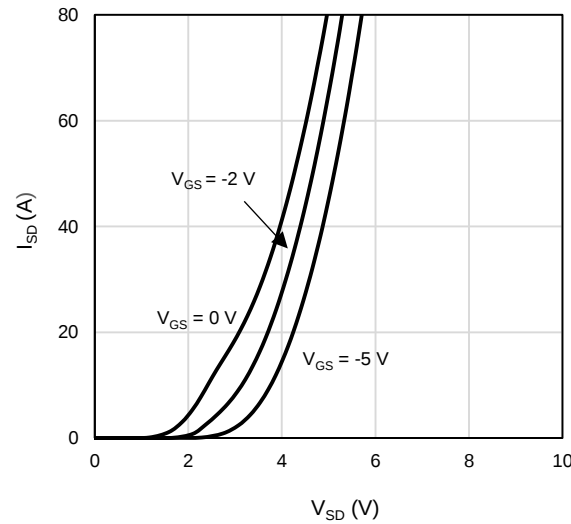


Figure 10: Body Diode Characteristics at 175°C

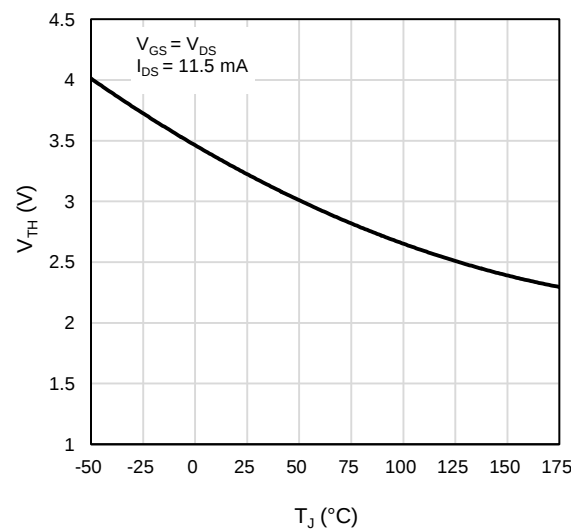


Figure 11: Threshold Voltage vs. Temperature

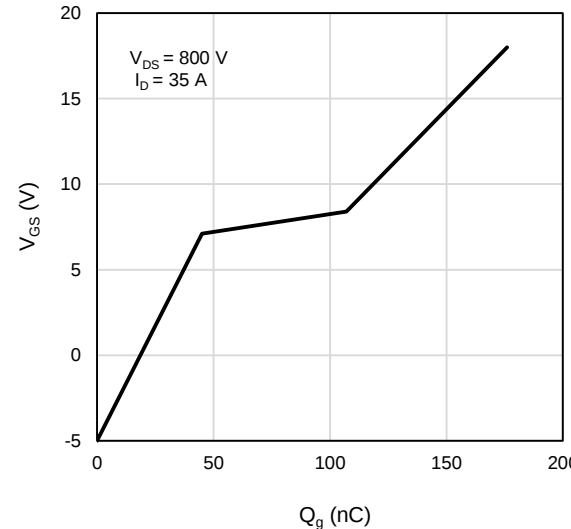


Figure 12: Gate-Charge Characteristics

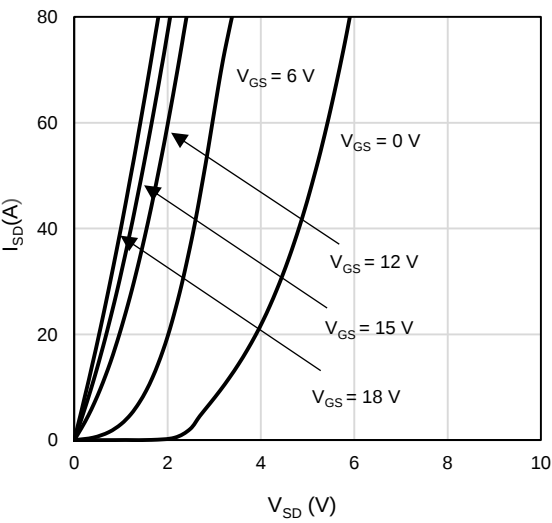


Figure 13: 3rd Quadrant Characteristics at -40°C

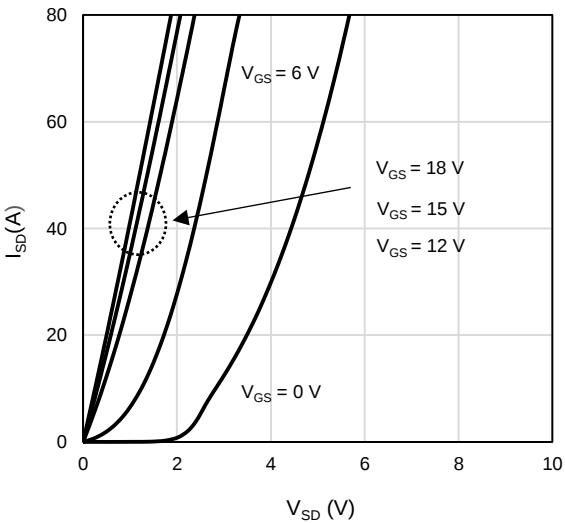


Figure 14: 3rd Quadrant Characteristics at 25°C

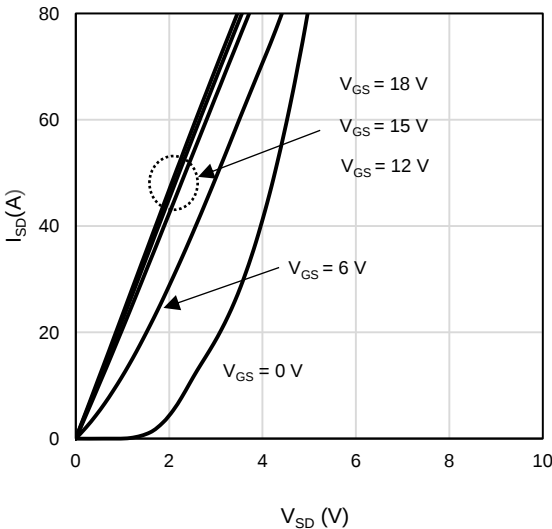


Figure 15: 3rd Quadrant Characteristics at 175°C

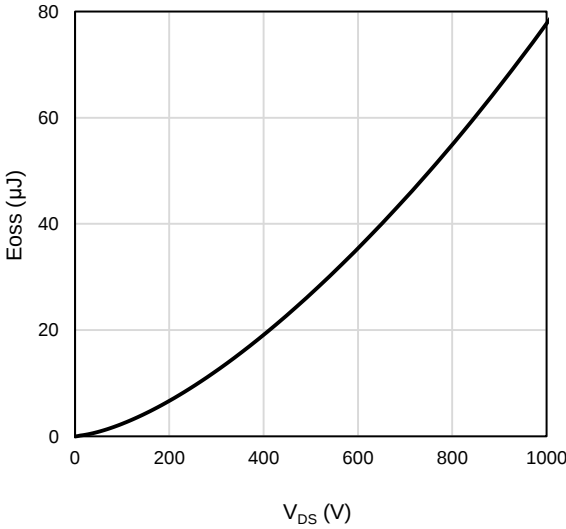


Figure 16: Output Capacitor Stord Energy

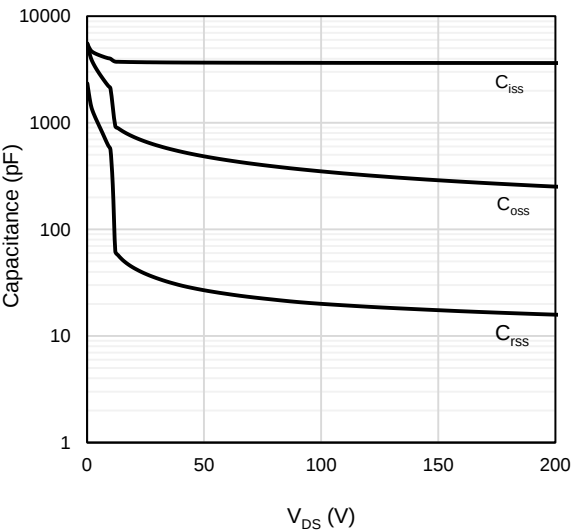


Figure 17: Capacitance Characteristics (0 - 200 V)

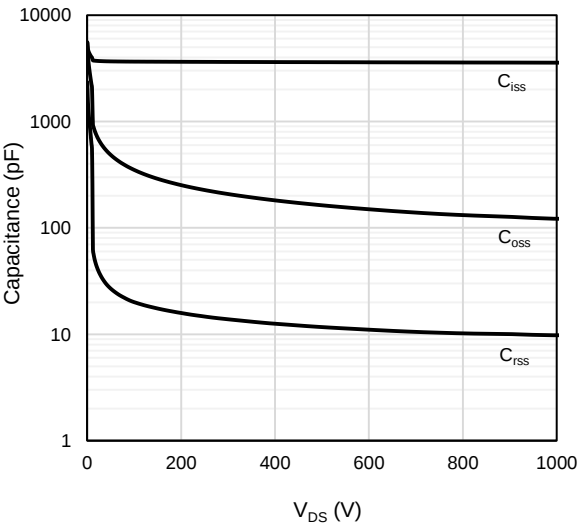


Figure 18: Capacitance Characteristics (0 - 1000 V)

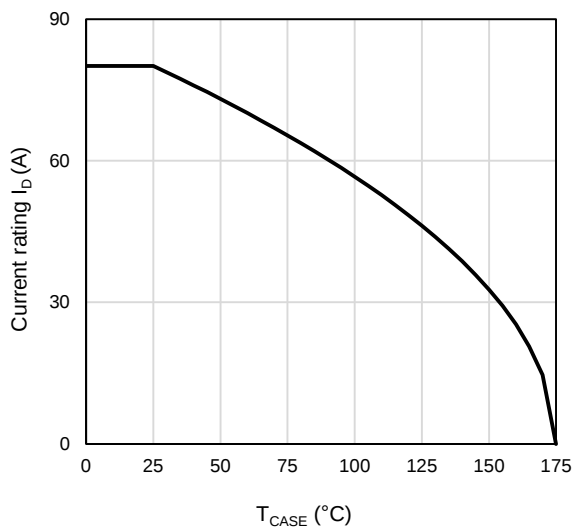


Figure 19: Current De-rating

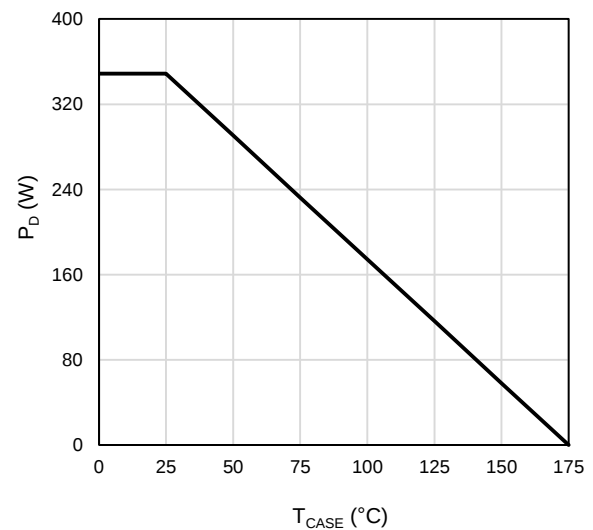


Figure 20: Maximum Power Dissipation Derating vs. CaseTemperature

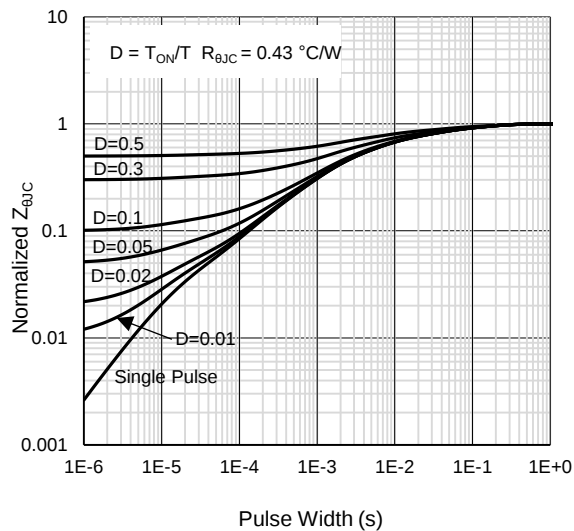


Figure 21: Normalized Maximum Transient Thermal Impedance

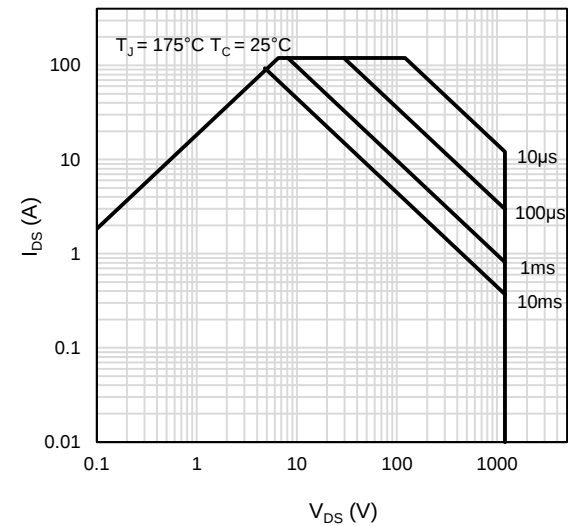
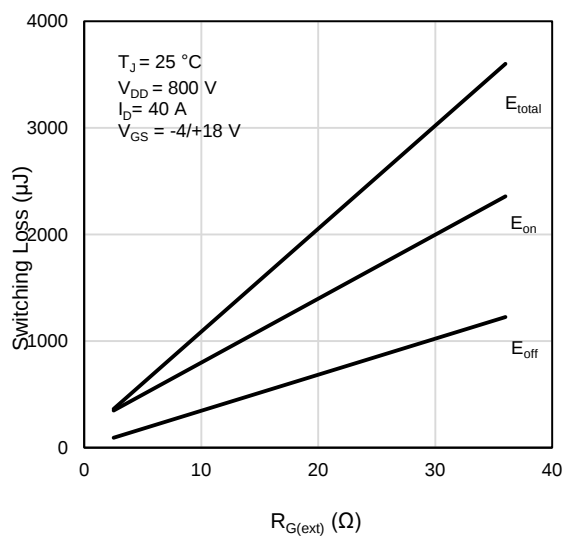
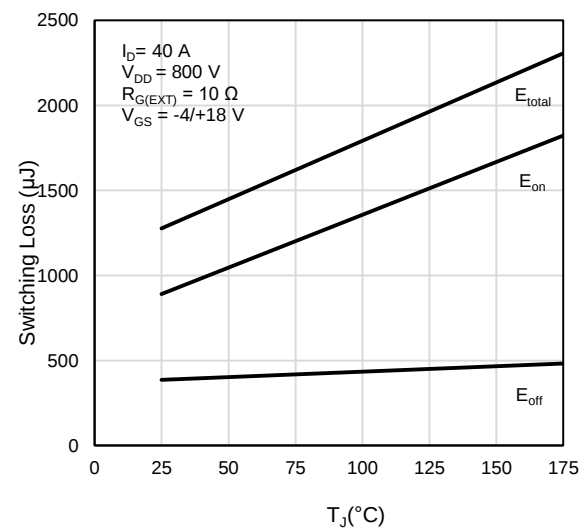


Figure 22: Maximum Forward Biased Safe Operating Area

Figure 23: Clamped Inductive Switching Energy vs. $R_{G(ext)}$ Figure 24: Clamped Inductive Switching Energy vs. T_J

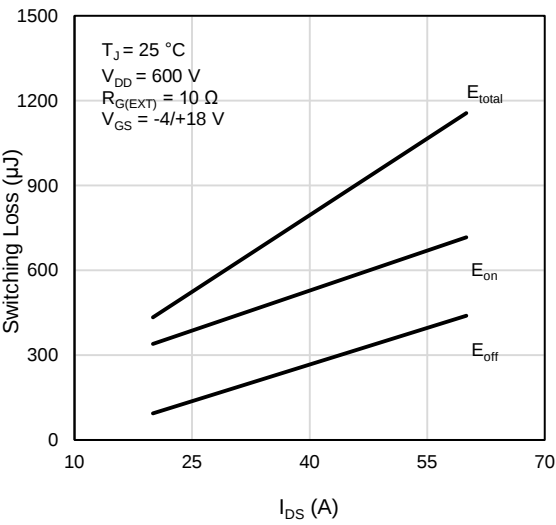


Figure 25: Clamped Inductive Switching Energy vs. Drain Current ($V_{\text{DD}} = 600\text{ V}$)

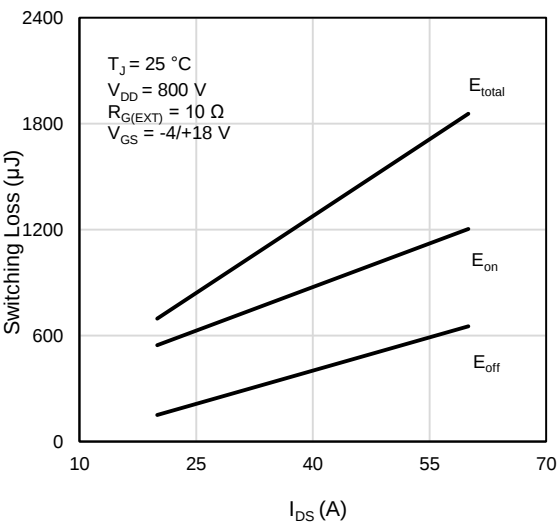
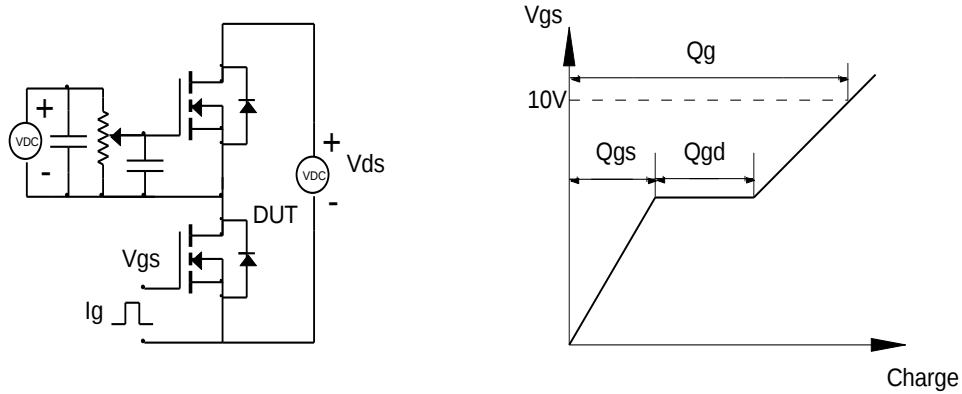


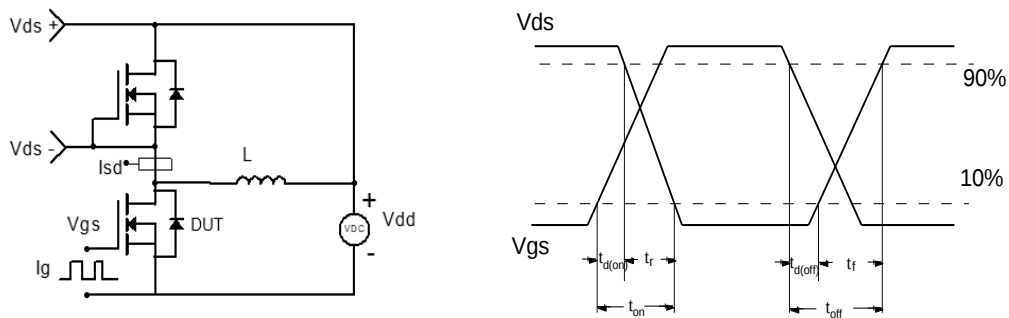
Figure 26: Clamped Inductive Switching Energy vs. Drain Current ($V_{\text{DD}} = 800\text{ V}$)

Test Circuit and Waveform

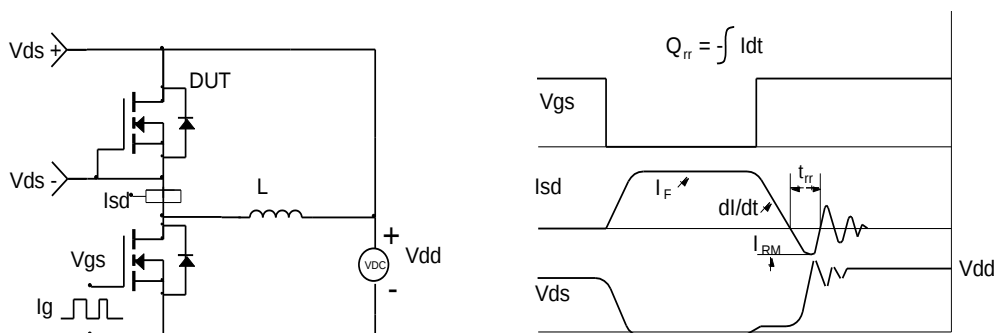
Gate Charge Test Circuit & Waveform



Clamped Inductive Switching Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



Revision History		
Revision	Released	Remark
Rev.1.0	2024	Initial Release

Disclaimer

The information given in this document describes the independent performance of the product, but similar performance is not guaranteed under other working conditions, and cannot be guaranteed when installed with other products or equipment. To achieve the required performance of the product in actual scenarios, the customer should conduct a complete application test to assess the functionality of the product.

Alkaidsemi assumes no responsibility for equipment failures result from using products at values that exceed the ratings, operating conditions, or other parameters listed in the product specifications.

The product described in this specification is not applicable for aerospace or other applications which requires high reliability. Customers using or selling these products for use in medical, life-saving, or life-sustaining applications do so at their own risk and agree to fully indemnify.

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